



US007419839B2

(12) **United States Patent**
Camras et al.

(10) **Patent No.:** **US 7,419,839 B2**
(45) **Date of Patent:** **Sep. 2, 2008**

(54) **BONDING AN OPTICAL ELEMENT TO A
LIGHT EMITTING DEVICE**

4,988,579 A 1/1991 Tomomura et al.
5,040,868 A 8/1991 Waitl et al.
5,055,892 A 10/1991 Gardner et al.
5,130,531 A 7/1992 Ito et al.

(75) Inventors: **Michael D. Camras**, Sunnyvale, CA
(US); **William R. Imler**, Oakland, CA
(US); **Frank S. Wall, Jr.**, Vacaville, CA
(US); **Frank M. Steranka**, San Jose, CA
(US); **Michael R. Krames**, Mountain
View, CA (US); **Helena Ticha**, Srch
(CZ); **Ladislav Tichy**, Srch (CZ)

(Continued)

FOREIGN PATENT DOCUMENTS

EP 0926744 A2 6/1999

(73) Assignee: **Philips Lumileds Lighting Company,
LLC**, San Jose, CA (US)

(Continued)

OTHER PUBLICATIONS

(*) Notice: Subject to any disclaimer, the term of this
patent is extended or adjusted under 35
U.S.C. 154(b) by 234 days.

Chui et al., "High-Efficiency AlGaInP Light-Emitting Diodes",
Semiconductor And Semimetals, vol. 64, Chapter 2, pp. 49-128.

(Continued)

(21) Appl. No.: **10/987,241**

Primary Examiner—Phuc T Dang

(22) Filed: **Nov. 12, 2004**

(57) **ABSTRACT**

(65) **Prior Publication Data**

US 2006/0105478 A1 May 18, 2006

(51) **Int. Cl.**
H01L 21/00 (2006.01)

(52) **U.S. Cl.** **438/22**; 438/24; 438/25

(58) **Field of Classification Search** 438/22,
438/24, 25, 26, 27, 28, 30

See application file for complete search history.

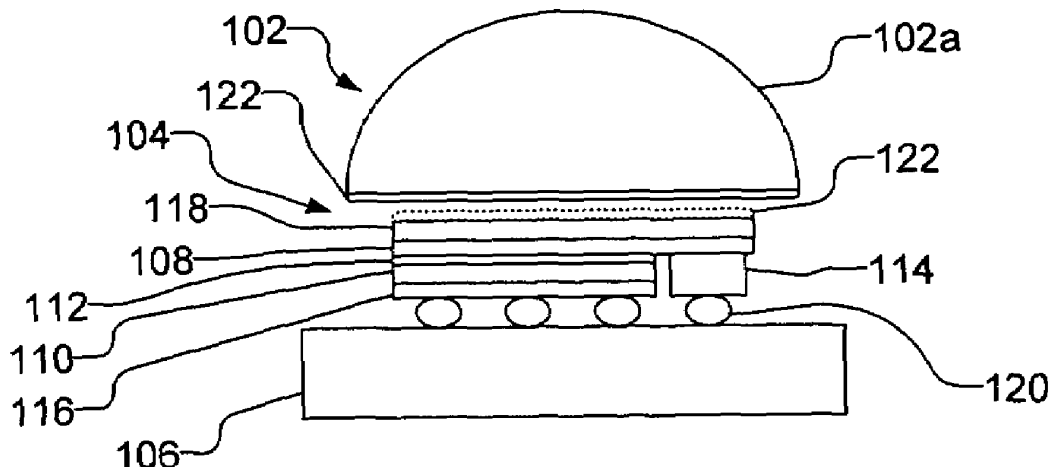
(56) **References Cited**

U.S. PATENT DOCUMENTS

3,769,536 A 10/1973 Antypas et al.
4,391,683 A 7/1983 Buckley et al.
4,675,058 A 6/1987 Plaster
4,689,652 A 8/1987 Shimada et al.
4,815,084 A 3/1989 Scifres et al.
4,983,009 A 1/1991 Musk

A device is provided with at least one light emitting device (LED) die mounted on a submount with an optical element subsequently thermally bonded to the LED die. The LED die is electrically coupled to the submount through contact bumps that have a higher temperature melting point than is used to thermally bond the optical element to the LED die. In one implementation, a single optical element is bonded to a plurality of LED dice that are mounted to the submount and the submount and the optical element have approximately the same coefficients of thermal expansion. Alternatively, a number of optical elements may be used. The optical element or LED die may be covered with a coating of wavelength converting material. In one implementation, the device is tested to determine the wavelengths produced and additional layers of the wavelength converting material are added until the desired wavelengths are produced.

37 Claims, 6 Drawing Sheets



US 7,419,839 B2

Page 2

U.S. PATENT DOCUMENTS

5,132,430	A	7/1992	Gaudiana et al.	
5,255,171	A	10/1993	Clark	
5,317,170	A	5/1994	Paoli	
5,376,580	A	12/1994	Kish et al.	
5,418,384	A	5/1995	Yamana et al.	
5,502,316	A	3/1996	Kish et al.	
5,528,057	A	6/1996	Yanagase et al.	
5,553,089	A	9/1996	Seki et al.	
5,661,316	A	8/1997	Kish et al.	
5,698,452	A	12/1997	Goossen	
5,724,376	A	3/1998	Kish, Jr. et al.	
5,779,924	A	7/1998	Krames et al.	
5,793,062	A	8/1998	Kish, Jr. et al.	
5,837,561	A	11/1998	Kish, Jr. et al.	
5,875,205	A	2/1999	Spaeth et al.	
5,898,185	A	4/1999	Bojarczuk, Jr. et al.	
5,917,201	A	6/1999	Ming-Jiunn et al.	
5,925,898	A	7/1999	Späth	
5,966,399	A	10/1999	Jiang et al.	
6,015,719	A	1/2000	Kish, Jr. et al.	
6,075,627	A	6/2000	Feldman et al.	
6,091,020	A	7/2000	Fairbanks et al.	
6,091,694	A	7/2000	Späth	
6,155,699	A	12/2000	Miller et al.	
6,165,911	A	12/2000	Calvey	
6,214,733	B1	4/2001	Sickmiller	
6,233,267	B1	5/2001	Nurmiko et al.	
6,412,971	B1	7/2002	Wojnarowski et al.	
6,429,462	B1	8/2002	Shveykin	
6,469,785	B1	10/2002	Duveneck et al.	
6,473,554	B1	10/2002	Pelka et al.	
6,483,196	B1	11/2002	Wojnarowski et al.	
6,495,862	B1	12/2002	Okazaki et al.	
6,576,488	B2 *	6/2003	Collins et al.	438/29
6,598,998	B2	7/2003	West et al.	
7,157,746	B2 *	1/2007	Ota et al.	257/100
2002/0030194	A1	3/2002	Camras et al.	
2002/0093023	A1 *	7/2002	Camras et al.	257/94
2002/0141006	A1	10/2002	Pocius et al.	
2003/0227249	A1	12/2003	Mueller et al.	
2004/0051106	A1	3/2004	Baur et al.	
2004/0223315	A1 *	11/2004	Suehiro et al.	362/84
2005/0274967	A1 *	12/2005	Martin et al.	257/98

2006/0012299 A1 * 1/2006 Suehiro et al. 313/512

FOREIGN PATENT DOCUMENTS

JP	09153645	6/1997
JP	09167515 A	6/1997
WO	WO 00/69000	11/2000
WO	WO 00/70687	11/2000
WO	WO 01/41219	6/2001
WO	WO 01/41225	6/2001
WO	WO 01/80322	10/2001
WO	WO 02/37578	5/2002

OTHER PUBLICATIONS

Babic et al., "Room-Temperature Continuous-Wave Operation of 1.54- μ m Vertical-Cavity Lasers", IEEE Photonics Technology Letters, vol. 7, No. 11, Nov. 1995, pp. 1225-1227.

Chua et al., "Dielectrically-Bonded Long Wavelength Vertical Cavity Laser on GaAs Substrates Using Strain-Compensated Multiple Quantum Wells", IEEE Photonics Technology Letters, vol. 6, No. 12, Dec. 1994, pp. 1400-1402.

Fischer et al., "Highly Refractive Glasses to Improve Electroluminescent Diode Efficiencies", Journal of the Electrochemical Society: Solid State Science, Dec. 1969, pp. 1718-1722.

Carr, "Photometric Figures of Merit for Semiconductor Luminescent Sources Operating in Spontaneous Mode", Infrared Physics, 1966, vol. 6, pp. 1-19.

Mary T. Strzelecki et al., "Low Temperature Bonding of Glasses and Glass Ceramics", 8 pages.

Robert D. Simpson et al., "Hybrid Glass Structures For Telecommunication Applications", 8 pages.

Joseph S. Hayden, Passive and Active Characterization of Hybrid Glass Substrates for Telecommunication Applications, 8 pages.

J.W. Osenbach, et al., Low Cost/High Volume Laser Modules Using Silicon Optical Bench Technology, 1998 Electronic Components and Technology Conference, p. 581.

Aluminum Oxide, Al₂O₃ For Optical Coating, CERAC, Inc. Technical Publications, pp. 1-4.

"Bulk Measurement", Sairon Technology, Inc., pp. 1-3.

Thomas R. Anthony, "Dielectric isolation of silicon by anodic bonding", J. Appl. Phys. vol. 58, No. 3, Aug. 1, 1985, pp. 1240-1247.

Joshua Israelsohn, "Switching the light fantastic", Tech Trends, EDN, Oct. 26, 2000, 10 pages.

Boris A. Matveev et al., "III-V Optically Pumped Mid-IR LEDs," Light-Emitting Diodes: Research, Manufacturing, and Applications, V.H. Walter Yao, E. Fred Schubert Editors, Proceedings of SPIE vol. 4278 (2001), pp. 189-196.

* cited by examiner

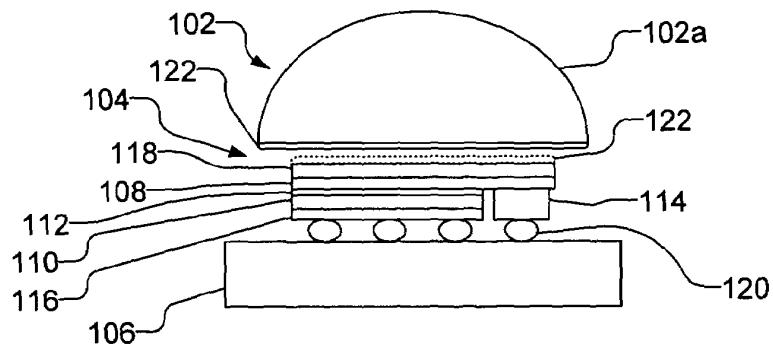


Fig. 1A

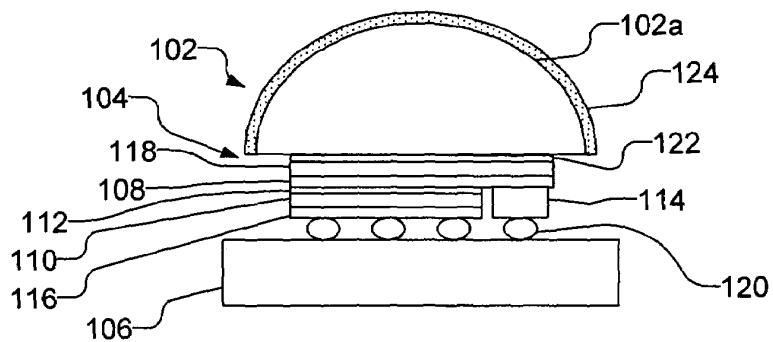


Fig. 1B

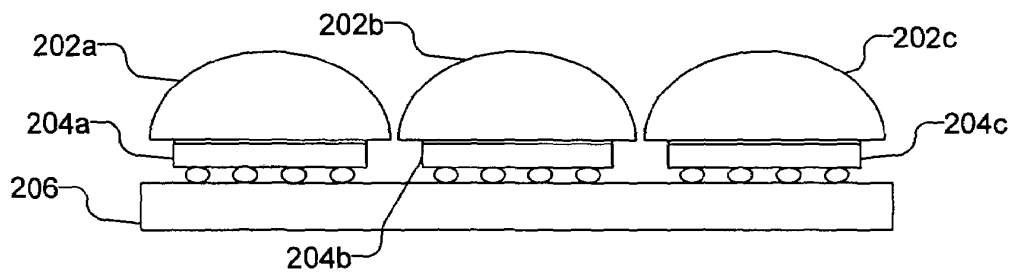


Fig. 2

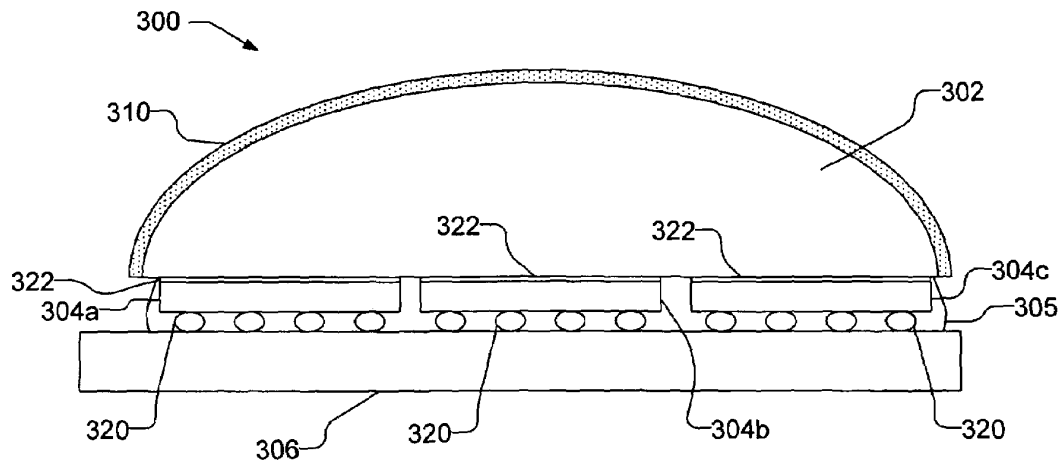


Fig. 3

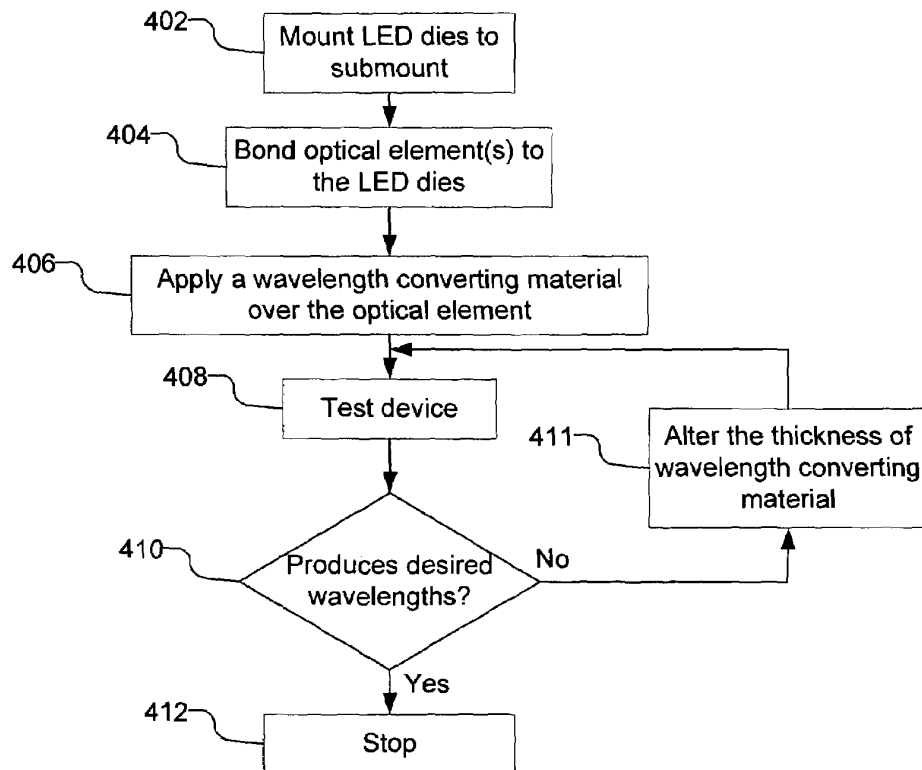


Fig. 4

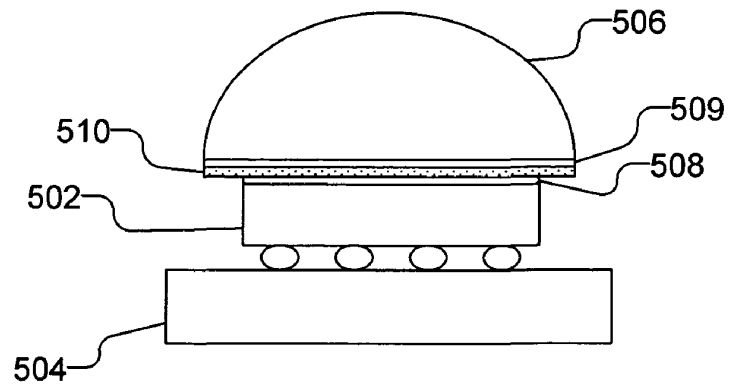


Fig. 5

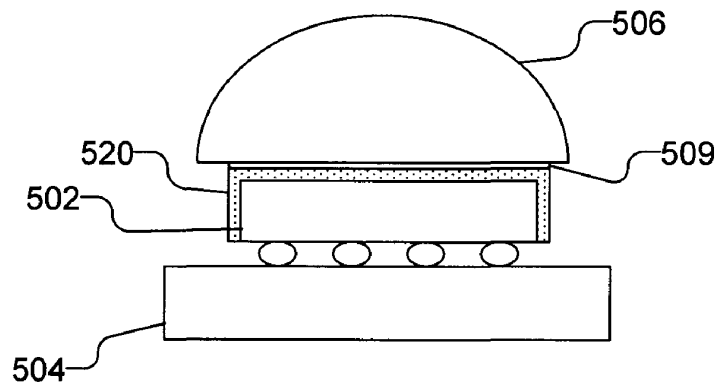


Fig. 6

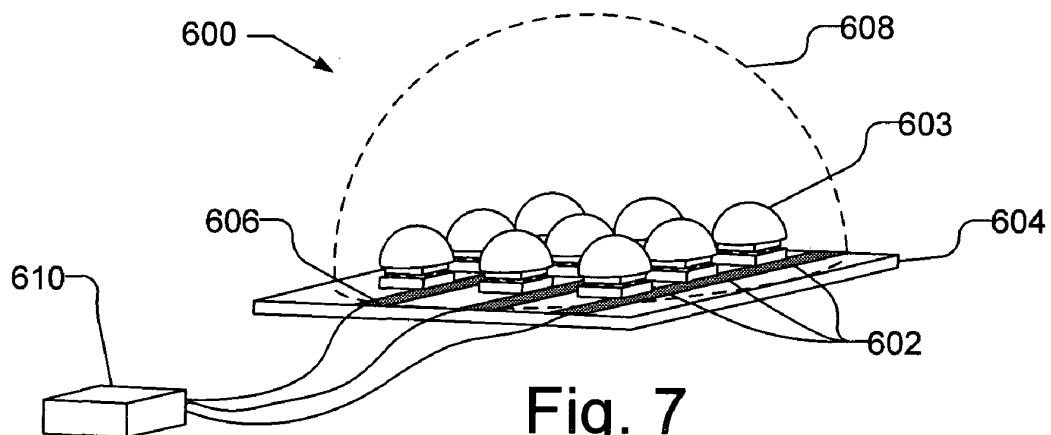


Fig. 7

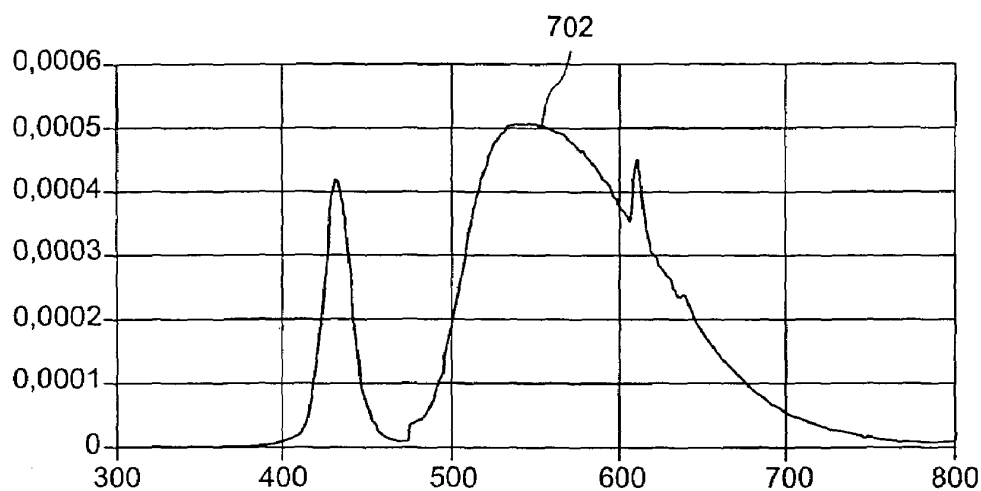


Fig. 8

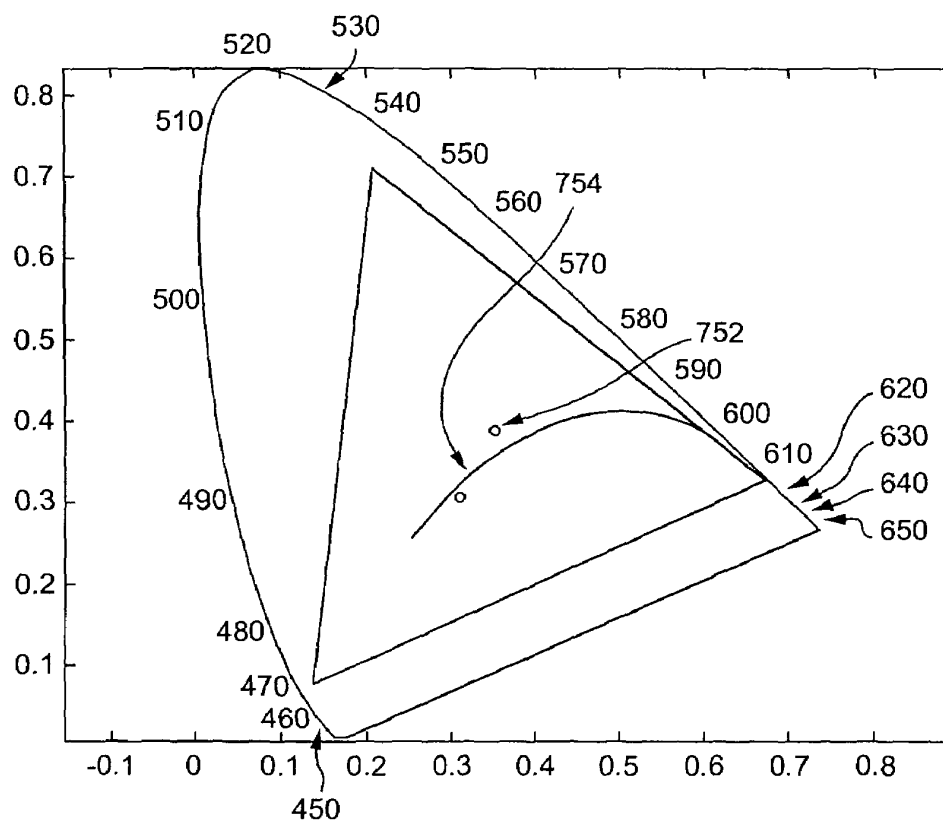


Fig. 9

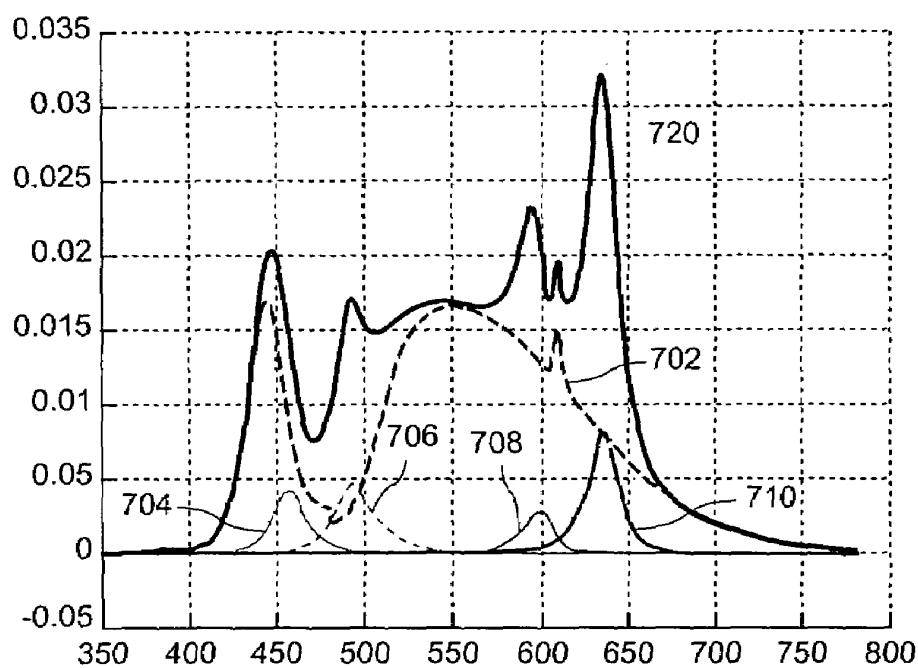


Fig. 10

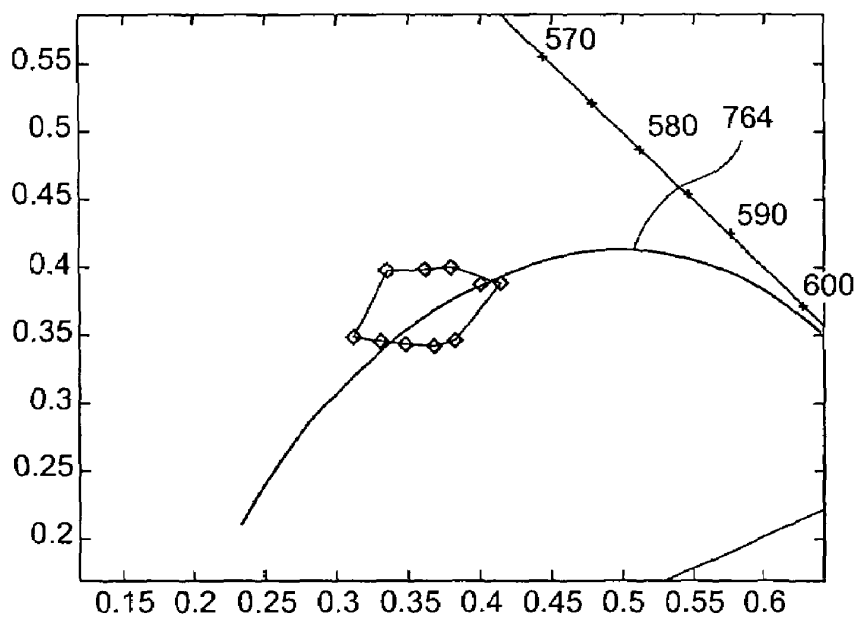


Fig. 11

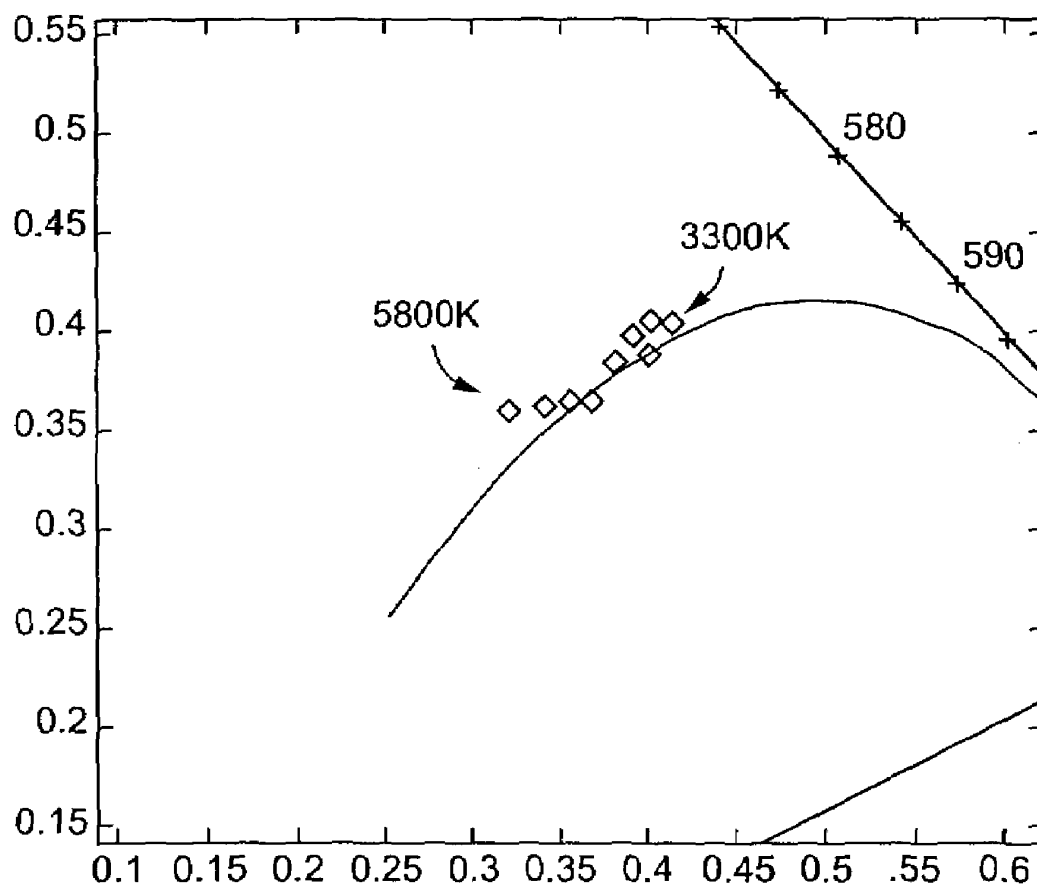


Fig. 12

1

BONDING AN OPTICAL ELEMENT TO A LIGHT EMITTING DEVICE

FIELD OF THE INVENTION

The present invention relates generally to light emitting devices and, more particularly, to bonding an optical element to one or more light emitting device dice.

BACKGROUND

Semiconductor light emitting devices (LEDs) are typically covered with an optical element to protect the semiconductor structures, increase light extraction efficiency, and assist in focusing the emitted light. One type of material used to encapsulate LEDs is epoxy. Epoxy, however, is a low refractive index material and thus is not as effective as a higher index material at reducing losses due to total internal reflection at the semiconductor/low index encapsulant interface. Further, epoxy and other organic encapsulants typically suffer from yellowing when used with LEDs that operate with high temperature and/or short wavelengths. Moreover, epoxy encapsulants typically have coefficients of thermal expansion that poorly match those of the semiconductor materials in the LED. Consequently, the epoxy encapsulant subjects the LED to mechanical stress upon heating or cooling and may damage the LED.

Thus, an improved optical element with increased light extraction efficiency and is resistant to yellowing or other degradation and a method of bonding such an optical element to an LED is desirable.

SUMMARY

In accordance with one embodiment of the present invention, a device is produced by mounting at least one light emitting device (LED) die on a submount and subsequently bonding an optical element to the LED die. The LED die is electrically coupled to the submount through contact elements, such as solder bumps or pads, that have a higher temperature melting point than is used to bond the optical element to the LED die. In one implementation, a single optical element is bonded to a plurality of LED dice that are mounted to the submount and the submount and the optical element have approximately the same coefficients of thermal expansion. Alternatively, a number of optical elements may be used. The LED or the optical element may be covered with a coating of wavelength converting material. In one implementation, the device is tested to determine the wavelengths produced and the thickness of the wavelength converting material is altered, i.e., increased or possibly decreased, until the desired wavelengths are produced.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1A illustrates a side view of an LED die mounted on a submount and an optical element that is to be bonded to the LED die.

FIG. 1B illustrates the optical element bonded to the LED die.

FIG. 2 illustrates an embodiment in which multiple LED dice are mounted to a submount and a separate optical element is bonded to each LED die.

FIG. 3 illustrates an embodiment in which multiple LED dice are mounted to a submount and a single optical element is bonded to the LED dice.

2

FIG. 4 is a flow chart of one implementation of producing such an LED device with wavelength converting material covering the optical element.

FIG. 5 illustrates an embodiment in which a layer of wavelength converting material is disposed between the bonding layer and the optical element.

FIG. 6 illustrates an embodiment in which a layer of wavelength converting material is deposited on the LED die.

FIG. 7 illustrates an array of LEDs, which are mounted on a board.

FIG. 8 is a graph of the broad spectrum produced by a phosphor converted blue LED.

FIG. 9 is a CIE chromaticity diagram for the spectrum shown in FIG. 8.

FIG. 10 is a graph of the spectra produced by phosphor converted LEDs and colored LEDs, which are combined to produce an approximately continuous spectrum.

FIG. 11 is a portion of a CIE chromaticity diagram that shows the variation in the CCT that may be produced by varying the brightness of the colored LEDs.

FIG. 12 is a portion of another CIE chromaticity diagram that illustrates variable CCT values for an array of 29 phosphor converted LEDs and 12 color LEDs.

DETAILED DESCRIPTION

FIG. 1A illustrates a side view of a transparent optical element **102** and a light emitting diode (LED) die **104** that is mounted on a submount **106**. The optical element **102** is to be bonded to the LED die **104** in accordance with an embodiment of the present invention. FIG. 1B illustrates the optical element **102** bonded to the LED die **104**.

The term "transparent" is used herein to indicate that the element so described, such as a "transparent optical element," transmits light at the emission wavelengths of the LED with less than about 50%, preferably less than about 10%, single pass loss due to absorption or scattering. The emission wavelengths of the LED may lie in the infrared, visible, or ultraviolet regions of the electromagnetic spectrum. One of ordinary skill in the art will recognize that the conditions "less than 50% single pass loss" and "less than 10% single pass loss" may be met by various combinations of transmission path length and absorption constant.

LED die **104** illustrated in FIGS. 1A and 1B includes a first semiconductor layer **108** of n-type conductivity (n-layer) and a second semiconductor layer **110** of p-type conductivity (p-layer). Semiconductor layers **108** and **110** are electrically coupled to an active region **112**. Active region **112** is, for example, a p-n diode junction associated with the interface of layers **108** and **110**. Alternatively, active region **112** includes one or more semiconductor layers that are doped n-type or p-type or are undoped. LED die **104** includes an n-contact **114** and a p-contact **116** that are electrically coupled to semiconductor layers **108** and **110**, respectively. Contact **114** and contact **116** are disposed on the same side of LED die **104** in a "flip chip" arrangement. A transparent superstrate **118** coupled to the n layer **108** is formed from a material such as, for example, sapphire, SiC, GaN, GaP, diamond, cubic zirconia (ZrO₂), aluminum oxynitride (AlON), AlN, spinel, ZnS, oxide of tellurium, oxide of lead, oxide of tungsten, polycrystalline alumina oxide (transparent alumina), and ZnO.

Active region **112** emits light upon application of a suitable voltage across contacts **114** and **116**. In alternative implementations, the conductivity types of layers **108** and **110**, together with respective contacts **114** and **116**, are reversed. That is, layer **108** is a p-type layer, contact **114** is a p-contact, layer **110** is an n-type layer, and contact **116** is an n-contact.

Semiconductor layers **108** and **110** and active region **112** may be formed from III-V semiconductors including but not limited to AlN, AlP, AlAs, AlSb, GaN, GaP, GaAs, GaSb, InN, InP, InAs, InSb, II-VI semiconductors including but not limited to ZnS, ZnSe, CdSe, ZnO, CdTe, group IV semiconductors including but not limited to Ge, Si, SiC, and mixtures or alloys thereof.

Contacts **114** and **116** are, in one implementation, metal contacts formed from metals including but not limited to gold, silver, nickel, aluminum, titanium, chromium, platinum, palladium, rhodium, rhenium, ruthenium, tungsten, and mixtures or alloys thereof.

Although FIGS. 1A and 1B illustrate a particular structure of LED die **104**, the present invention is independent of the structure of the LED die. Accordingly, other types of LED configurations may be used instead of the specific configuration shown. Further, the number of semiconductor layers in LED die **104** and the detailed structure of active region **112** may differ. It should be noted that dimensions of the various elements of LED die **104** illustrated in the various figures are not to scale.

The LED die **104** is mounted to submount **106** via contact elements **120**, such as solder bumps, pads, or other appropriate elements, such as a layer of solder. Contact elements **120** will be sometimes referred to herein as bumps **120** for the sake of simplicity. Bumps **120** are manufactured from Au, Sn, Ag, Sb, Cu, Pb, Bi, Cd, In, Zn or alloys thereof including AuSn, SnSb, SnCu, SnAg, SnAgBi, InSn, BiPbSn, BiPbCd, BiPbIn, InCd, BiPb, BiSn, InAg, BiCd, InBi, InGa, or other appropriate material with a melting temperature that is greater than the temperature that will be used to bond the optical element **102** to the LED die **104**, but is preferably Au or AuSn. In one implementation, the melting temperature of bumps **120** is greater than 250° C. and preferably greater than 300° C. The submount **106** may be, e.g., silicon, alumina or AlN and may include vias for backside connections.

The LED die **104** is mounted to the submount **106**, e.g., using thermosonic bonding. For example, during the thermosonic bonding process, the LED die **104** with bumps **120** are aligned with the submount **106** in the desired position while the submount **106** is heated to approximately 150-160° C. A bond force of, e.g., approximately 50-100 gm/bump, is applied to the LED die **104** by a bonding tool, while ultrasonic vibration is applied. If desired other processes may be used, such as thermo-compression, to bond the LED die **104** to the submount **106**. As is well known in the art, with thermo-compression higher temperatures and greater bonding forces are typically required.

In some embodiments, an underfill may be used with the LED die **104** and submount **106**. The underfill material may have good thermal conductivity and have a coefficient of thermal expansion that approximately matches the LED die **104** and the submount **106**. In another embodiment, a protective side coat, e.g., of silicone or other appropriate material, may be applied to the sides of the LED die **104** and the submount **106**. The protective side coating acts as a sealant and limits exposure of the LED **104** and the bumps **120** to contamination and the environment.

For more information regarding producing bumps **120** from Au or Au/Sn and for submounts with backside vias and bonding LED dice with Au or Au/Sn bumps to a submount, see U.S. Ser. No. 10/840,459, by Ashim S. Haque, filed May 5, 2004, which has the same assignee as the present disclosure and is incorporated herein by reference. It should be understood, however, that the present invention is not limited to any specific type of submount and that any desired submount configuration may be used if desired.

After the LED die **104** is mounted to the submount **106**, the optical element **102** is thermally bonded to the LED die **104**. In one embodiment, a layer of bonding material is applied to the bottom surface of the optical element **102** to form transparent bonding layer **122** that is used to bond optical element **102** to LED die **104**. In some embodiments, the transparent bonding layer **122** may be applied to the top surface of the LED die **104**, e.g., to superstrate **118**, (as indicated by the dotted lines **122** in FIG. 1A). The bonding layer **122** can be applied to the LED die **104** prior to or after mounting the LED die **104** to the submount **106**. Alternatively, no bonding layer may be used and the optical element **102** may be bonded directly to the LED die **104**, e.g., the superstrate **118**. The transparent bonding layer **122** is, for example, about 10 Angstroms (Å) to about 100 microns (μm) thick, and is preferably about 1000 Å to about 10 μm thick, and more specifically, about 0.5 μm to about 5 μm thick. The bonding material is applied, for example, by conventional deposition techniques including but not limited to spinning, spraying, sputtering, evaporation, chemical vapor deposition (CVD), or material growth by, for example, metal-organic chemical vapor deposition (MOCVD), vapor phase epitaxy (VPE), liquid phase epitaxy (LPE), or molecular beam epitaxy (MBE). In one embodiment, the optical element **102** may be covered with a wavelength converting material **124**, which will be discussed in more detail below.

In one implementation, the bonding material from which transparent bonding layer **122** is formed from glass such as SF59, LaSF 3, LaSF N18, SLAH51, LAF10, NZK7, NLAF21, LASFN35, SLAM60, or mixtures thereof, which are available from manufactures such as Schott Glass Technologies Incorporated, of Duryea, Pa. and Ohara Corporation in Somerville, N.J. Bonding layer **122** may also be formed from a high index glass, such as (Ge, As, Sb, Ga)(S, Se, Te, Cl, Br) chalcogenide or chalcogen-halogenide glasses, for example.

In other implementations, bonding layer **122** may be formed from III-V semiconductors including but not limited to GaP, InGaP, GaAs, and GaN; II-VI semiconductors including but not limited to ZnS, ZnSe, ZnTe, CdS, CdSe, and CdTe; group IV semiconductors and compounds including but not limited to Si, and Ge; organic semiconductors, metal oxides including but not limited to oxides of antimony, bismuth, boron, copper, niobium, tungsten, titanium, nickel, lead, tellurium, phosphor, potassium, sodium, lithium, zinc, zirconium, indium tin, or chromium; metal fluorides including but not limited to magnesium fluoride, calcium fluoride, potassium fluoride, sodium fluoride, and zinc fluoride; metals including but not limited to Zn, In, Mg, and Sn; yttrium aluminum garnet (YAG), phosphide compounds, arsenide compounds, antimonide compounds, nitride compounds, high index organic compounds; and mixtures or alloys thereof.

In implementations where the LED die **104** is configured with the n-contact and p-contact on opposite sides of the die **104**, the transparent bonding layer **122** or **122'** may be patterned with, for example, conventional photolithographic and etching techniques to leave the top contact uncovered by bonding material and thus to permit contact to make electrical contact with a metallization layer on the optical element **102**, which may serve as a lead, as is described in U.S. Ser. No. 09/880,204, filed Jun. 12, 2001, by Michael D. Camras et al., entitled "Light Emitting Diodes with Improved Light Extraction Efficiency" having Pub. No. 2002/0030194, which is incorporated herein by reference.

In one implementation, the optical element **102** is formed from optical glass, high index glass, GaP, CZ, ZnS, SiC,

sapphire, diamond, cubic zirconia (ZrO₂), ALON, by Sienna Technologies, Inc., polycrystalline aluminum oxide (transparent alumina), spinel, Schott glass LaFN21, Schott glass LaSFN35, LaF2, LaF3, and LaF10 available from Optimax Systems Inc. of Ontario, N.Y., an oxide of Pb, Te, Zn, Ga, Sb, Cu, Ca, P, La, Nb, or W, or any of the materials listed above for use as bonding materials in transparent bonding layer 122, excluding thick layers of the metals.

The transparent optical element 102 may have a shape and a size such that light entering optical element 102 from LED die 104 will intersect surface 102a of optical element 102 at angles of incidence near normal incidence. Total internal reflection at the interface of surface 102a and the ambient medium, typically air, is thereby reduced. In addition, since the range of angles of incidence is narrow, Fresnel reflection losses at surface 102a can be reduced by applying a conventional antireflection coating to the surface 102a. The shape of optical element 102 is, for example, a portion of a sphere such as a hemisphere, a Weierstrass sphere (truncated sphere), or a portion of a sphere less than a hemisphere. Alternatively, the shape of optical element 102 is a portion of an ellipsoid such as a truncated ellipsoid. The angles of incidence at surface 102a for light entering optical element 102 from LED die 4 more closely approach normal incidence as the size of optical element 102 is increased. Accordingly, the smallest ratio of a length of the base of transparent optical element 102 to a length of the surface of LED die 104 is preferably greater than about 1, more preferably greater than about 2.

After the LED die 104 is mounted on the submount 106, the optical element 102 is thermally bonded to the LED die 104. For example, to bond the optical element 102 to the LED die 104, the temperature of bonding layer 122 is raised to a temperature between about room temperature and the melting temperature of the contact bumps 120, e.g., between approximately 150° C. to 450° C., and more particularly between about 200° C. and 400° C., and optical element 102 and LED die 104 are pressed together at the bonding temperature for a period of time of about one second to about 6 hours, preferably for about 30 seconds to about 30 minutes, at a pressure of about 1 pound per square inch (psi) to about 6000 psi. By way of example, a pressure of about 700 psi to about 3000 psi may be applied for between about 3 to 15 minutes.

The thermal bonding of the optical element 102 to the LED die 104 requires the application of elevated temperatures. With the use of bumps 120 that have a high melting point, i.e., higher than the elevated temperature used in the thermal bonding process, the LED die 104 may be mounted to the submount 106 before the optical element 102 is bonded to the LED die 104 without damaging the LED die/submount connection. Mounting the LED die 104 to the submount 106 prior to bonding the optical element 102 simplifies the pick and place process.

Bonding an optical element 102 to an LED die 104 is described in US Pub. No. 2002/0030194; Ser. No. 10/633, 054, filed Jul. 31, 2003, by Michael D. Camras et al., entitled "Light Emitting Devices with Improved Light Extraction Efficiency"; Ser. No. 09/660,317, filed Sep. 12, 2000, by Michael D. Camras et al., entitled "Light Emitting Diodes with Improved Light Extraction Efficiency"; Ser. No. 09/823, 841, filed Mar. 30, 2001, by Douglas Pocius, entitled "Forming an Optical Element on the Surface of a Light Emitting Device for Improved Light Extraction" having Pub. No. 2002/0141006, which have the same assignee as the present application and which are incorporated herein by reference. Further, the process of bonding optical element 102 to LED die 104 described above may be performed with devices disclosed in U.S. Pat. Nos. 5,502,316 and 5,376,580, incor-

porated herein by reference, previously used to bond semiconductor wafers to each other at elevated temperatures and pressures. The disclosed devices may be modified to accommodate LED dice and optical elements, as necessary. Alternatively, the bonding process described above may be performed with a conventional vertical press.

It should be noted that due to the thermal bonding process, a mismatch between the coefficient of thermal expansion (CTE) of optical element 102 and LED die 104 can cause optical element 102 to detach from LED die 104 upon heating or cooling. Accordingly, optical element 102 should be formed from a material having a CTE that approximately matches the CTE of LED die 104. Approximately matching the CTEs additionally reduces the stress induced in the LED die 104 by bonding layer 122 and optical element 102. With suitable CTE matching, thermal expansion does not limit the size of the LED die that may be bonded to the optical element and, thus, the optical element 102 may be bonded to a large LED die 104, e.g., up to 16 mm² or larger.

FIG. 2 illustrates an embodiment in which multiple LED dice 204a, 204b, and 204c (sometimes collectively referred to as LED dice 204) are mounted on a submount 206. The LED dice 204 are schematically illustrated in FIG. 2 without showing the specific semiconductor layers. Nevertheless, it should be understood that the LED dice 204 may be similar to LED die 104 discussed above.

The LED dice 204 are each mounted to submount 206 as described above. Once the LED dice 204 are mounted on submount 206, individual optical elements 202a, 202b, and 202c are bonded to LED dice 204a, 204b, and 204c, respectively, in a manner such as that described above.

If desired, the LED dice 204 may be the same type of LED and may produce the same wavelengths of light. In another implementation, one or more of the LED dice 204 may produce different wavelengths of light, which when combined may be used to produce light with a desired correlated color temperature (CCT), e.g., white light. Another optical element (not shown in FIG. 2) may be used to cover optical elements 202a, 202b, and 202c and aid in mixing the light.

FIG. 3 illustrates an embodiment of an LED device 300 that includes multiple LED dice 304a, 304b, and 304c (sometimes collectively referred to as LED dice 304) mounted on a submount 306 and a single optical element 302 bonded to the LED dice 304. The LED dice 304 may be similar to LED die 104 discussed above.

The use of a single optical element 302 with multiple LED dice 304, as shown in FIG. 3, is advantageous as the LED dice 304 can be mounted close together on submount 306. Optical components typically have a larger footprint than an LED die to which it is bonded, and thus, the placement of LED dice with separate optical elements is constrained by the size of the optical elements.

After the LED dice 304 are mounted to the submount, there may be slight height variations in the top surfaces of the LED dice 304, e.g., due to the differences in the height of the bumps 320 and thickness of the dice. When the single optical element 302 is thermally bonded to the LED dice 304, any differences in the height of the LED dice 304 may be accommodated by the compliance of the bumps 320.

During the thermal bonding process of the optical element 302 to the LED dice 304, the LED dice 304 may shift laterally due to the heating and cooling of the submount 306. With the use of some bumps 320, such as Au, the compliance of the bumps 320 can be inadequate to accommodate lateral shift of the LED dice 304. Accordingly, the coefficient of thermal expansion of the optical element 302 (CTE₃₀₂) should approximately match the coefficient of thermal expansion of

7

the submount 306 (CTE₃₀₆). With an approximate match between CTE₃₀₂ and CTE₃₀₆ any movement of the LED dice 304 caused by the expansion and contraction of the submount 306 will be approximately matched by the expansion and contraction of the optical element 302. A mismatch between CTE₃₀₂ and CTE₃₀₆, on the other hand, can result in the detachment of the LED dice 304 from the optical element 302 or other damage to the LED device 300, during the heating and cooling of the thermal bonding process.

With the use of sufficiently small LED dice 304, the thermal expansion of the LED dice 304 themselves during the thermal bonding process may be minimized. With the use of large LED dice 304, however, the amount of thermal expansion of the LED dice 304 during the thermal bonding process may be large and thus, the CTE for the LED dice 304 also should be appropriately matched to the CTE of the submount 306.

The LED dice 304 may be, e.g., InGa_N, AlInGaP, or a combination of InGa_N and AlInGaP devices. In one implementation, the submount 302 may be manufactured from AlN, while the optical element 302 may be manufactured from, e.g., SLAM60 by Ohara Corporation, or NZK7 available from Schott Glass Technologies Incorporated. In another implementation, an Alumina submount 306 may be used along with an optical element 302 manufactured from sapphire, Ohara Glass SLAH51 or Schott glass NLAF21. In some implementations, a bulk filler 305 between the LED dice 304 and the submount 306 may be used. The bulk filler 305 may be, e.g., silicone or glass. The bulk filler 305 may have good thermal conductivity and may approximately match the CTE of the submount 306 and the dice 304. If desired, a protective side coating may be applied alternatively or in addition to the bulk filler 305.

In one implementation, all of the LED dice 304 may be the same type and produce different or approximately the same wavelengths of light. Alternatively, with an appropriate choice of LED dice 304 and/or wavelength conversion materials, different wavelengths of light may be produced, e.g., blue, green and red. When LED dice 304 are the same type, the CTE for the LED dice 304 will be approximately the same. It may be desirable for the CTE of the LED dice 304 to closely match the coefficient of thermal expansion of the optical element 302 and the submount 306 to minimize the risk of detachment or damage to the LED dice 304 during the thermal bonding process.

In another implementation, the LED dice 304 may be different types and produce different wavelengths of light. With the use of different types of LED dice, the CTE of the dice can vary making it difficult to match the CTE for all the LED dice 304 with that of the optical element 302 and the submount 306. Nevertheless, with a judicious choice of the optical element 302 and submount 306 with CTEs that are as close as possible to that of the LED dice 304, problems associated with detachment of the LED dice 304 or other damage to the device 300 during the thermal bonding process may be minimized. Additionally, with the use of relatively small LED dice 304, e.g., the area smaller than approximately 1 mm², problems associated with thermal bonding a single optical element 302 to multiple dice 304 may also be reduced. The use of a bulk filler 305 may also prevent damage to the device during thermal processing or operation.

As shown in FIG. 3, in one implementation, the optical element 302 may be coated with a wavelength converting material 310, such as a phosphor coating. In one embodiment, the wavelength converting material 310 is YAG. FIG. 4 is a flow chart of one implementation of producing such a device.

8

As illustrated in FIG. 4, the LED dice 304 are mounted to the submount 306 (step 402) and the optical element 302 is bonded to the LED dice 304 (step 404). After the optical element 302 is bonded to the LED dice 304, a layer of the wavelength converting material 310 is deposited over the optical element 302 (step 406). The device can then be tested, e.g., by applying a voltage across the active regions of the LED dice 304 and detecting the wavelengths of light produced by the device (step 408). If the device does not produce the desired wavelengths (step 410), the thickness of the wavelength converting material is altered (step 411), e.g., by depositing additional wavelength converting material 310 over the optical element 302 or by removing some of the wavelength converting material by etching or dissolution and the device is again tested (step 408). The process stops once the desired wavelengths of light are produced (step 412).

Thus, the thickness of the wavelength converting material 310 coating is controlled in response to the light produced by the LED dice 304 resulting in a highly reproducible correlated color temperature. Moreover, because the deposition of the wavelength converting material 310 is in response to the specific wavelengths produced by the LED dice 304, a variation in the wavelengths of light produced by LED dice 304 can be accommodated. Accordingly, fewer LED dice 304 will be rejected for producing light with wavelengths outside a useful range of wavelengths.

It should be understood that the process of coating the optical element with a wavelength converting material may be applied to the embodiments shown in FIGS. 1B and 2 as well.

In another implementation, the coating of wavelength converting material may be placed between the LED die and the optical element, e.g., within, over, or under the bonding layer 322. FIG. 5, by way of example, illustrates an LED die 502 mounted to a submount 504 and bonded to an optical element 506 via bonding layer 508, where a layer of wavelength converting material 510 is disposed between the bonding layer 508 and the optical element 506. The wavelength converting material 510 may be bonded to the bottom surface of the optical element 506 by bonding layer 509 prior to or during the bonding the optical element 506 to the LED die 502. The wavelength converting material 510 may be, e.g., a phosphor impregnated glass or wavelength converting ceramic that is formed independently and then bonded to the LED die 502 and optical element 506. In some embodiments, the wavelength converting material 510 may be bonded directly to one or both of the LED die 502 and optical element 506. In one embodiment, the optical element 506, LED die 502 and wavelength converting material 510 may be bonded together simultaneously. In another embodiment, the wavelength converting material 510 may be bonded first to the optical element 506 and subsequently bonded to the LED die 502, e.g., where the bonding layer 509 has a higher bonding temperature than the bonding layer 508. A suitable wavelength converting material, such as a phosphor impregnated glass, is discussed in more detail in U.S. Ser. No. 10/863,980, filed on Jun. 9, 2004, by Paul S. Martin et al., entitled "Semiconductor Light Emitting Device with Pre-Fabricated Wavelength Converting Element", which has the same assignee as the present application and is incorporated herein by reference.

FIG. 6 illustrates another embodiment, similar to the embodiment shown in FIG. 5, except a wavelength converting material 520 is bonded directly to the LED die 502 (and optionally over the edges of the LED die 502) prior to or during bonding of the optical element 506. Thus, as shown in FIG. 6, the wavelength converting material 520 is placed

between the LED die **502** and the bonding layer **509**. If desired, an additional layer of wavelength converting material may be deposited over the optical element **506** in FIGS. **5** and **6**, as discussed above.

In another implementation, the coating of wavelength converting material may be located over the LED die or dice remotely, e.g., on an envelope of glass, plastic, epoxy, or silicone with a hollow space between the envelope and the LED die or dice. If desired, the hollow space may be filled with a material such as silicone or epoxy.

FIG. **7** illustrates an array **600** of LEDs **602**, which are mounted on a board **604**. The board **604** includes electrical traces **606** that are used to provide electrical contact to the LEDs **602**. The LEDs **602** may be phosphor converted devices manufactured, e.g., as described above. The LEDs **602** may each produce white light with different CCTs. By mixing the white light with different CCTs in array **600**, a light with a desired CCT may be produced. If desired, the LEDs **602** may be covered with a transparent element **608** of e.g., glass, plastic, epoxy, or silicone. The transparent element **608** may be filled, e.g., with epoxy or silicone, which assists the extracting and mixing of the light and to protect the LEDs **602**. It should be understood that array **600** may include any number of LEDs **602** and that if desired, one or more of the LEDs may produce non-white light. Moreover, if desired, a plurality of the LEDs **602** may be bonded to a single optical element **603**, or one or more of the LEDs **602** may not include optical element **603**.

As illustrated in FIG. **7**, individual or groups of LEDs **602** maybe independently controlled, e.g., by controller **610**, which is electrically connected to the traces **606** on the board **604**. By independently controlling LEDs **602** or groups of LEDs **602**, a high color rendering, e.g., over **85**, with a constant brightness may be achieved. Further, the white points produced by the array **600** may be tuneable over a large range of CCT, e.g., between 3000K and 6000K. By way of example, a number of phosphor-converted (PC) blue LEDs that produce white light may be used in combination with LEDs with different colors, such as blue, cyan, amber and red to produce a light with a desired CCT. As shown in the graph of FIG. **8**, the phosphor converted blue LEDs generates light with a broad spectrum **702** in the green area in combination with a peak in the blue region. The thickness of the phosphor may be tuned to produce approximately equal peak values for both the green and blue parts of the spectrum. FIG. **9** shows a CIE chromaticity diagram for the spectrum shown in FIG. **8**, which illustrates the x and y color coordinates **752** above the black bodyline **754**. Of course, PC LEDs that produce spectra having peaks in other area may be used if desired. Alternatively, if desired, PC LEDs that produce different spectra, i.e., white light having different CCTs may be used together.

A majority of the LEDs **602** in the array **600** of FIG. **7** may be PC LEDs that generate the spectrum shown in FIG. **8**. The remaining LEDs **602** shown in FIG. **7** may be color LEDs, e.g., LEDs that produce blue, cyan, amber and red. The brightness of the color LEDs may be adjusted by controller **610**. The combination of fully powered PC LEDs with colored LEDs generates an approximately continuous spectrum, as illustrated in FIG. **10**. FIG. **10** shows a graph with the spectrum **702** from the PC LEDs along with spectra **704**, **706**, **708** and **710** from the blue, cyan, amber and red colored LEDs combined to form spectrum **720**. As illustrated in the portion of the CIE chromaticity diagram shown in FIG. **11**, by varying the brightness of the colored LEDs, an area that covers part of the black body line **764** can be obtained. By way of example, one embodiment that included 29 PC LEDs and 12 color LEDs is capable of producing a brightness of 800 lumen with

a color rendering between 85 and 95 and a CCT between 3200K and 5800K. FIG. **12** illustrates a portion of the CIE chromaticity diagram that illustrates variable CCT values for an array of 29 PC LEDs and 12 color LEDs. Of course, any number of PC LEDs and color LEDs may be used.

Although the present invention is illustrated in connection with specific embodiments for instructional purposes, the present invention is not limited thereto. Various adaptations and modifications may be made without departing from the scope of the invention. Therefore, the spirit and scope of the appended claims should not be limited to the foregoing description.

What is claimed is:

1. A method comprising:

mounting at least one light emitting device die to a submount through contact elements, the submount having a first coefficient of thermal expansion; and

bonding an optical element to the at least one light emitting device die after the light emitting device die is mounted to the submount, wherein the bonding of the optical element to the at least one light emitting device die is effected by a bonding layer disposed between the optical element and the at least one light emitting device die, the optical element having a second coefficient of thermal expansion, wherein the first coefficient of thermal expansion and the second coefficient of thermal expansion are sufficiently matched that the optical element does not detach from the light emitting device die due to differences in thermal expansion and contraction during bonding.

2. The method of claim 1, wherein the bonding layer comprises an inorganic material.

3. The method of claim 1, wherein bonding comprises:

elevating a temperature of the optical element, the bonding layer, the light emitting device die, and the submount to a temperature that is less than the melting temperature of the contact elements; and

applying a pressure to press the optical element and the light emitting device die together, thereby bonding the optical element to the light emitting device die through the bonding layer.

4. The method of claim 3, wherein the temperature is elevated to a temperature that is greater than the temperature used to mount the light emitting device die and the submount.

5. The method of claim 1, wherein the contact elements are on at least one of the bottom surface of the light emitting device die and the top surface of the submount, the contact elements providing electrical contact between the light emitting device die and the submount.

6. The method of claim 5, wherein the contact elements are at least one of bumps and pads formed from a material that includes at least one of Au and AuSn.

7. The method of claim 4, wherein the temperature used to mount the at least one light emitting device die to the submount is less than approximately 250° C.

8. The method of claim 1, wherein a temperature used to bond the optical element to the at least one light emitting device die is less than approximately 400° C.

9. The method of claim 1, wherein the bonding layer between the optical element and the light emitting device die comprises at least one of an oxide of tellurium, oxide of tungsten, oxide of lead, and oxide of zinc.

10. The method of claim 1, wherein the bonding layer between the optical element and the light emitting device die comprises at least one of an oxide of sodium, oxide of potassium, oxide of lithium, and fluoride of zinc.

11

11. The method of claim 1, wherein a plurality of light emitting device dice are mounted to the submount.

12. The method of claim 11, wherein one optical element is bonded to the plurality of light emitting device dice.

13. The method of claim 11, wherein a separate optical element is bonded to each of the plurality of light emitting device dice.

14. The method of claim 1, further comprising depositing a coating of wavelength converting material over the optical element.

15. The method of claim 14, wherein depositing a coating of wavelength converting material over the optical element comprises:

- depositing a layer of the wavelength converting material over the optical element;
- determining the wavelengths of light produced by the device when a forward biasing current is applied to the light emitting device die;
- repeatedly increasing the thickness of the layer of wavelength converting material and determining the wavelengths of light produced by the device until the desired wavelengths of light are produced.

16. The method of claim 1, further comprising placing a layer of wavelength converting material between the at least one light emitting device die and the optical element prior to bonding the optical element to the light emitting device die.

17. The method of claim 16, wherein the layer of wavelength converting material is bonded on at least one of the bottom surface of the optical element and the top surface of the light emitting device die.

18. The method of claim 1, wherein the optical element includes wavelength converting material.

19. The method of claim 1, wherein the light emitting device die comprises a stack of semiconductor layers, at least one of which is an active region that emits light, and a first contact and a second contact electrically coupled to apply a voltage across the active region; the first contact and the second contact disposed on a same side of the stack.

20. A method comprising:

- providing a submount having a first coefficient of thermal expansion;
- providing a plurality of light emitting device dice;
- mounting the plurality of light emitting device dice to the submount;
- providing an optical element having a second coefficient of thermal expansion that is approximately the same as the first coefficient of thermal expansion; and
- bonding the optical element to the plurality of light emitting device dice after the light emitting device dice are mounted to the submount.

21. The method of claim 20, wherein mounting the plurality of light emitting device dice to the submount is performed using one of thermo-compression and thermo-sonic bonding.

22. The method of claim 21, wherein bonding the optical element to the plurality of light emitting device dice comprises elevating a temperature of the optical element, the light emitting device dice and the submount to a temperature that is greater than that the temperature used to mount the plurality of light emitting device dice and the submount, and applying a pressure to press the optical element and the light emitting device dice together.

23. The method of claim 22, wherein at least one of the light emitting device dice and the submount include contact elements, the contact elements providing electrical contact between the light emitting device dice and the submount and wherein the temperature of bonding the optical element to the

12

plurality of light emitting device dice is less than the melting temperature of the contact elements.

24. The method of claim 23, wherein the contact elements are at least one of bumps and pads formed from a material that includes at least one of Au and AuSn.

25. The method of claim 21, wherein the coefficients of thermal expansion of the plurality of light emitting device dice are approximately the same as the first coefficient of thermal expansion.

26. The method of claim 20, further comprising depositing a coating of wavelength converting material over the optical element.

27. The method of claim 26, wherein depositing a coating of wavelength converting material over the optical element comprises:

- depositing a layer of the wavelength converting material over the optical element;
- determining the wavelengths of light produced by the device when a forward biasing current is applied to the light emitting device die;
- repeatedly increasing the thickness of the layer of wavelength converting material and determining the wavelengths of light produced by the device until the desired wavelengths of light are produced.

28. The method of claim 20, wherein each of the light emitting device dice comprise a stack of semiconductor layers, at least one of which is an active region that emits light, and a first contact and a second contact electrically coupled to apply a voltage across the active region; the first contact and the second contact disposed on a same side of the stack.

29. A method comprising:

- mounting at least one light emitting device die to a submount with contact elements, wherein the light emitting device die is mounted to the submount at a first temperature; and
- bonding an optical element to the at least one light emitting device die after the light emitting device die is mounted to the submount, wherein the optical element is bonded to the light emitting device die at a second temperature that is greater than the first temperature.

30. The method of claim 29, wherein the light emitting device die is mounted to the submount thermosonically.

31. The method of claim 29, wherein the second temperature is between approximately 150° C. and 450° C.

32. The method of claim 29, wherein the contact elements melt at a third temperature and wherein the second temperature is less than the third temperature.

33. The method of claim 29, wherein the contact elements are at least one of bumps and pads formed from a material that includes at least one of Au and AuSn.

34. A method comprising:

- providing a semiconductor light emitting device comprising a stack of semiconductor layers including an active region;
- providing an optical element, the optical element having a coefficient of thermal expansion;
- bonding the semiconductor light emitting device to the optical element effected by a bonding layer disposed between the optical element and the semiconductor light emitting device, wherein the bonding layer comprises a material selected from the group of an oxide of tellurium, an oxide of lead, an oxide of tungsten, and an oxide of zinc; and
- bonding the semiconductor light emitting device to a submount before bonding the semiconductor light emitting device to the optical element, the submount having a coefficient of thermal expansion that is sufficiently

13

matched with the coefficient of thermal expansion of the optical element so that the optical element does not detach from the light emitting device die due to differences in thermal expansion and contraction during bonding.

35. The method of claim **34**, wherein the temperature used to bond the light emitting device to the optical element is between about 200° C. and 400° C.

14

36. The method of claim **34**, wherein the time that the optical element and light emitting device are at bonding temperature is between about 30 seconds and 30 minutes.

37. The method of claim **34**, wherein the pressure used to bond the light emitting device to the optical element is between about 700 and 3000 psi.

* * * * *